International
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# IRF9383MPbF

## DirectFET® P-Channel Power MOSFET ②

### Applications

- Isolation Switch for Input Power or Battery Application
- High Side Switch for Inverter Applications

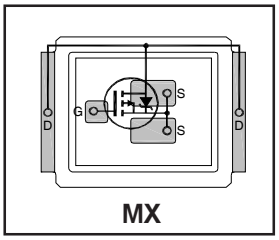
### Features and Benefits

- Environmentaly Friendly Product
- RoHs Compliant Containing no Lead, no Bromide and no Halogen
- Common-Drain P-Channel MOSFETs Provides High Level of Integration and Very Low RDS(on)

**Typical values (unless otherwise specified)**

| $V_{DSS}$ | $V_{GS}$ | $R_{DS(on)}$ | $R_{DS(on)}$ |
|---|---|---|---|
| -30V max | ±20V max | 2.3mΩ@-10V | 3.8mΩ@-4.5V |

| $Q_{g\ tot}$ | $Q_{gd}$ | $Q_{gs2}$ | $Q_{rr}$ | $Q_{oss}$ | $V_{gs(th)}$ |
|---|---|---|---|---|---|
| 67nC | 29nC | 9.4nC | 315nC | 59nC | -1.8V |



MX

DirectFET™ ISOMETRIC

Applicable DirectFET Outline and Substrate Outline (see p.7,8 for details)①

| SQ | SX | ST | | MQ | **MX** | MT | MP | MC | | |
|---|---|---|---|---|---|---|---|---|---|---|

## Description

The IRF9383MTRPbF combines the latest HEXFET® P-Channel Power MOSFET Silicon technology with the advanced DirectFET® packaging to achieve the lowest on-state resistance in a package that has the footprint of a SO-8 and only 0.6 mm profile. The DirectFET® package is compatible with existing layout geometries used in power applications, PCB assembly equipment and vapor phase, infra-red or convection soldering techniques, when application note AN-1035 is followed regarding the manufacturing methods and processes. The DirectFET® package allows dual sided cooling to maximize thermal transfer in power systems, improving previous best thermal resistance by 80%.

| Orderable part number | Package Type | Standard Pack | | Note |
|---|---|---|---|---|
| | | Form | Quantity | |
| IRF9383MTRPbF | DirectFET® Medium Can | Tape and Reel | 4800 | |
| ~~IRF9383MTR1PbF~~ | ~~DirectFET® Medium Can~~ | ~~Tape and Reel~~ | ~~1000~~ | ~~"TR1" suffix~~ EOL notice #264 |

## Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---|---|---|---|
| $V_{DS}$ | Drain-to-Source Voltage | -30 | V |
| $V_{GS}$ | Gate-to-Source Voltage | ±20 | |
| $I_D$ @ $T_A$ = 25°C | Continuous Drain Current, $V_{GS}$ @ 10V ③ | -22 | A |
| $I_D$ @ $T_A$ = 70°C | Continuous Drain Current, $V_{GS}$ @ 10V ③ | -17 | |
| $I_D$ @ $T_C$ = 25°C | Continuous Drain Current, $V_{GS}$ @ 10V ④ | -160 | |
| $I_{DM}$ | Pulsed Drain Current ⑤ | -180 | |

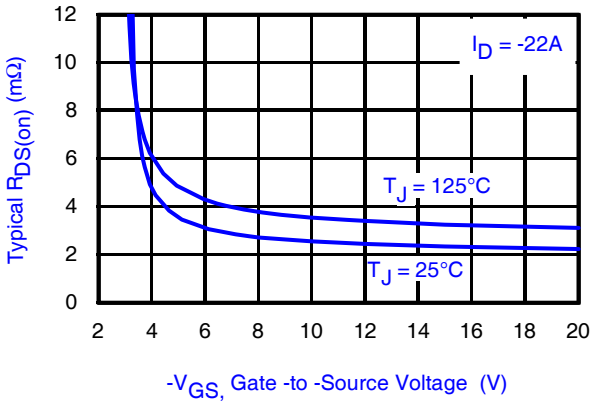



**Fig 1.** Typical On-Resistance vs. Gate Voltage

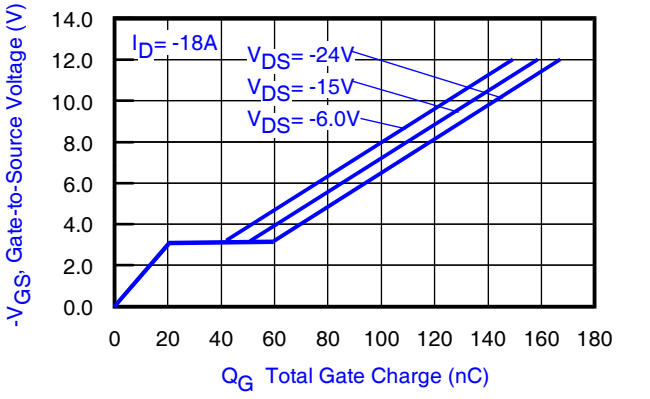



**Fig 2.** Typical Total Gate Charge vs Gate-to-Source Voltage

Notes:

① Click on this section to link to the appropriate technical paper.

② Click on this section to link to the DirectFET® Website.

③ Surface mounted on 1 in. square Cu board, steady state.

④ $T_C$ measured with thermocouple mounted to top (Drain) of part.

⑤ Repetitive rating; pulse width limited by max. junction temperature.

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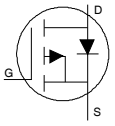
## Static @ $T_J$ = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---|---|---|---|---|---|---|
| $BV_{DSS}$ | Drain-to-Source Breakdown Voltage | -30 | — | — | V | $V_{GS}$ = 0V, $I_D$ = -250µA |
| $\Delta BV_{DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 0.0159 | — | V/°C | Reference to 25°C, $I_D$ = -1.0mA |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | — | 2.3 | 2.9 | mΩ | $V_{GS}$ = -10V, $I_D$ = -22A ⑥ |
| | | — | 3.8 | 4.8 | | $V_{GS}$ = -4.5V, $I_D$ = -18A ⑥ |
| $V_{GS(th)}$ | Gate Threshold Voltage | -1.3 | -1.8 | -2.4 | V | $V_{DS}$ = $V_{GS}$, $I_D$ = -150µA |
| $\Delta V_{GS(th)}/\Delta T_J$ | Gate Threshold Voltage Coefficient | — | -5.9 | — | mV/°C | |
| $I_{DSS}$ | Drain-to-Source Leakage Current | — | — | -1.0 | µA | $V_{DS}$ = -24V, $V_{GS}$ = 0V |
| | | — | — | -150 | | $V_{DS}$ = -24V, $V_{GS}$ = 0V, $T_J$ = 125°C |
| $I_{GSS}$ | Gate-to-Source Forward Leakage | — | — | -100 | nA | $V_{GS}$ = -20V |
| | Gate-to-Source Reverse Leakage | — | — | 100 | | $V_{GS}$ = 20V |
| gfs | Forward Transconductance | 56 | — | — | S | $V_{DS}$ = -10V, $I_D$ = -18A |
| $Q_g$ | Total Gate Charge | — | 130 | — | nC | $V_{DS}$ = -15V, $V_{GS}$ = -10V, $I_D$ = -18A |
| $Q_g$ | Total Gate Charge | — | 67 | — | | $V_{DS}$ = -15V<br>$V_{GS}$ = -4.5V<br>$I_D$ = -18A<br>See Fig.15 |
| $Q_{gs1}$ | Pre- Vth Gate-to-Source Charge | — | 12 | — | | |
| $Q_{gs2}$ | Post -Vth Gate-to-Source Charge | — | 9.4 | — | | |
| $Q_{gd}$ | Gate-to-Drain Charge | — | 29 | — | | |
| $Q_{godr}$ | Gate Charge Overdrive | — | 16.6 | — | | |
| $Q_{sw}$ | Switch charge ($Q_{gs2}$ + $Q_{gd}$) | — | 38.4 | — | | |
| $Q_{oss}$ | Output Charge | — | 59 | — | nC | $V_{DS}$ = -24V, $V_{GS}$ = 0V |
| $R_G$ | Gate Resistance | — | 6.5 | — | Ω | |
| $t_{d(on)}$ | Turn-On Delay Time | — | 29 | — | ns | $V_{DD}$ = -15V, $V_{GS}$ = -4.5V ⑥<br>$I_D$ = -18A<br>$R_G$ = 1.8Ω<br>See Fig.17 |
| $t_r$ | Rise Time | — | 160 | — | | |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 115 | — | | |
| $t_f$ | Fall Time | — | 110 | — | | |
| $C_{iss}$ | Input Capacitance | — | 7305 | — | pF | $V_{GS}$ = 0V<br>$V_{DS}$ = -15V<br>$f$ = 1.0KHz |
| $C_{oss}$ | Output Capacitance | — | 1780 | — | | |
| $C_{rss}$ | Reverse Transfer Capacitance | — | 1030 | — | | |

## Diode Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---|---|---|---|---|---|---|
| $I_S$ | Continuous Source Current (Body Diode) | — | — | -114 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| $I_{SM}$ | Pulsed Source Current (Body Diode) ⑤ | — | — | -180 | | |
| $V_{SD}$ | Diode Forward Voltage | — | — | -1.2 | V | $T_J$ = 25°C, $I_S$ = -18A, $V_{GS}$ = 0V ⑥ |
| $t_{rr}$ | Reverse Recovery Time | — | 52 | 78 | ns | $T_J$ = 25°C, $I_F$ = -18A, ,$V_{DD}$ = -15V |
| $Q_{rr}$ | Reverse Recovery Charge | — | 315 | 470 | nC | di/dt = 500A/µs ⑥ |

**Notes:**

⑥ Pulse width ≤ 400µs; duty cycle ≤ 2%.

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## Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---|---|---|---|
| $P_D$ @$T_A$ = 25°C | Power Dissipation ③ | 2.1 | W |
| $P_D$ @$T_A$ = 70°C | Power Dissipation ③ | 1.3 | |
| $P_D$ @$T_C$ = 25°C | Power Dissipation ④ | 113 | |
| $T_P$ | Peak Soldering Temperature | 270 | °C |
| $T_J$<br>$T_{STG}$ | Operating Junction and<br>Storage Temperature Range | -40 to + 150 | |

## Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|---|---|---|---|---|
| $R_{\theta JA}$ | Junction-to-Ambient ③ | — | 60 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient ⑦ | 12.5 | — | |
| $R_{\theta JA}$ | Junction-to-Ambient ⑧ | 20 | — | |
| $R_{\theta JC}$ | Junction-to-Case ④,⑨ | — | 1.1 | |
| $R_{\theta J\text{-}PCB}$ | Junction-to-PCB Mounted | 1.0 | — | |
| | Linear Derating Factor ③ | 0.02 | | W/°C |

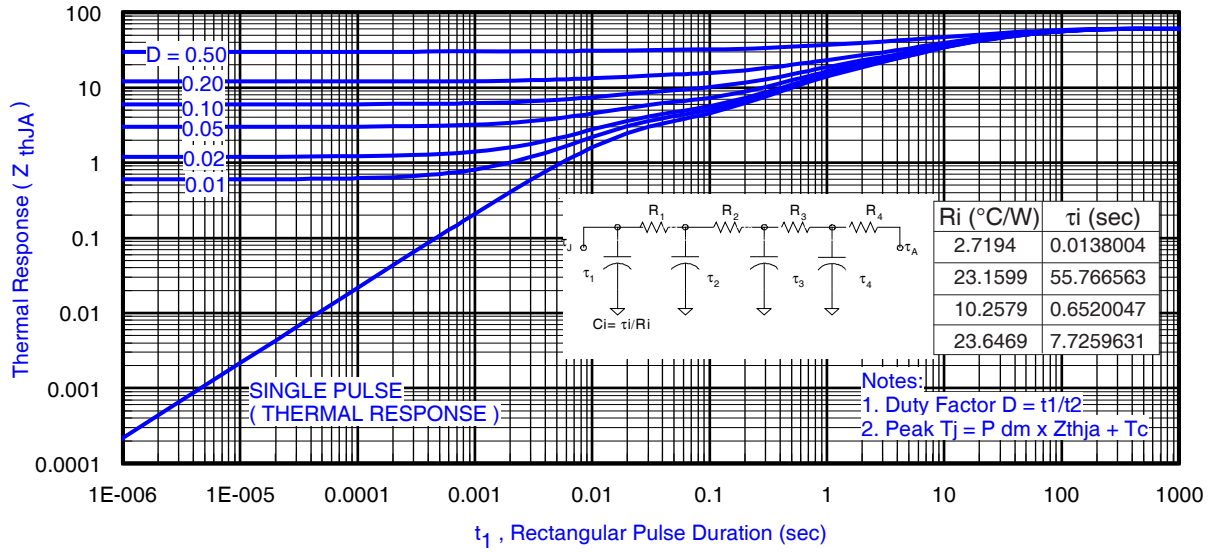


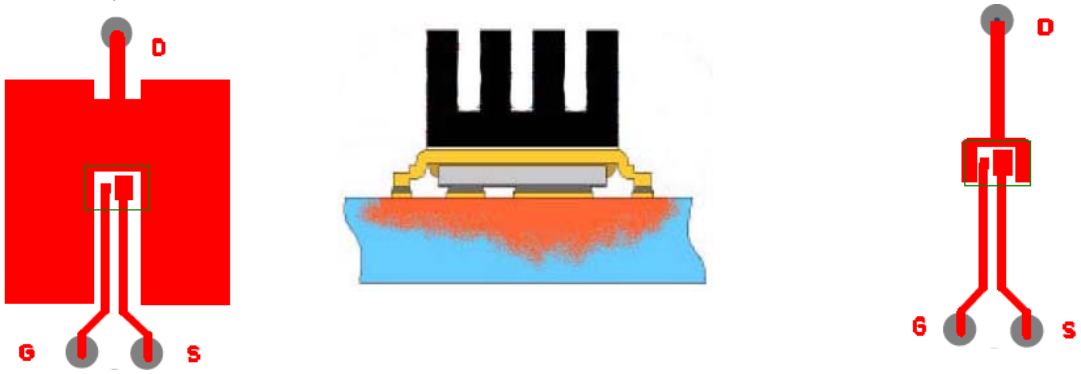

**Fig 3.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient ①

**Notes:**

⑦ Used double sided cooling, mounting pad with large heatsink.

⑧ Mounted on minimum footprint full size board with metalized back and with small clip heatsink.

⑨ $R_\theta$ is measured at $T_J$ of approximately 90°C.




③ Surface mounted on 1 in. square Cu board (still air).

⑨ Mounted to a PCB with small clip heatsink (still air)

⑨ Mounted on minimum footprint full size board with metalized back and with small clip heatsink (still air)

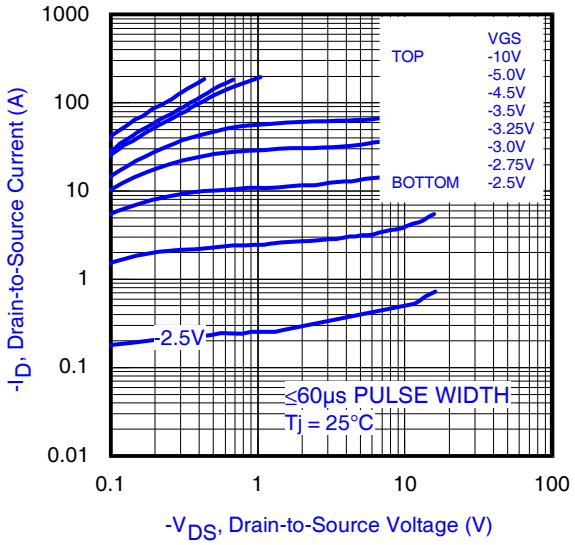



**Fig 4.** Typical Output Characteristics

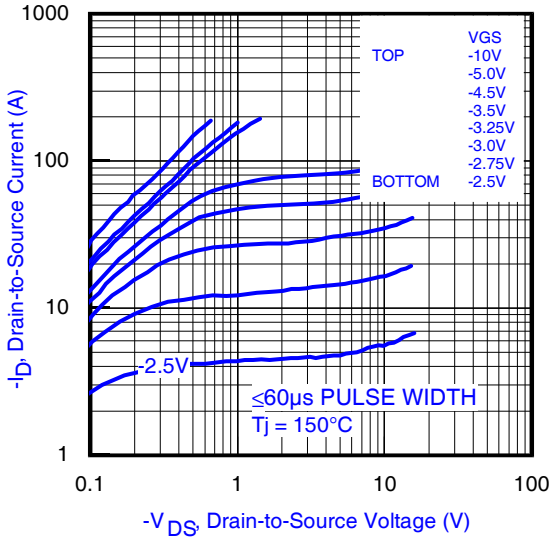



**Fig 5.** Typical Output Characteristics

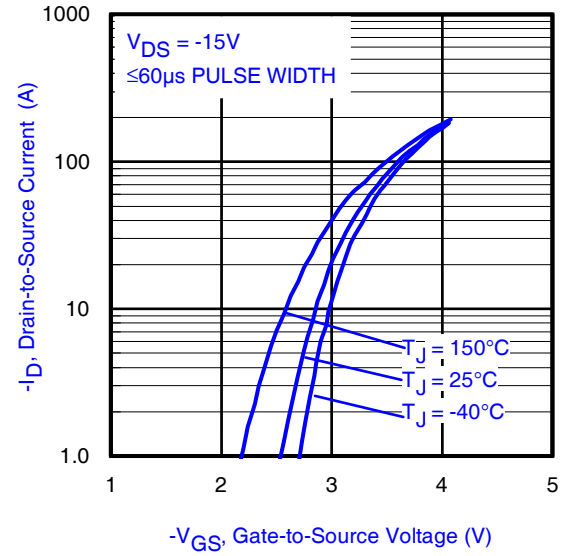



**Fig 6.** Typical Transfer Characteristics

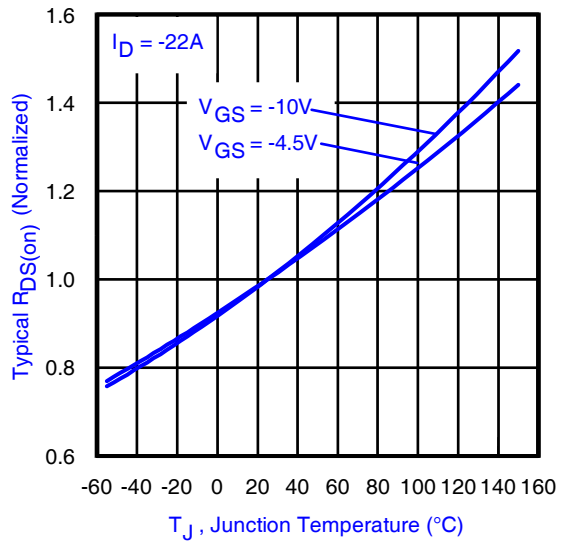



**Fig 7.** Normalized On-Resistance vs. Temperature

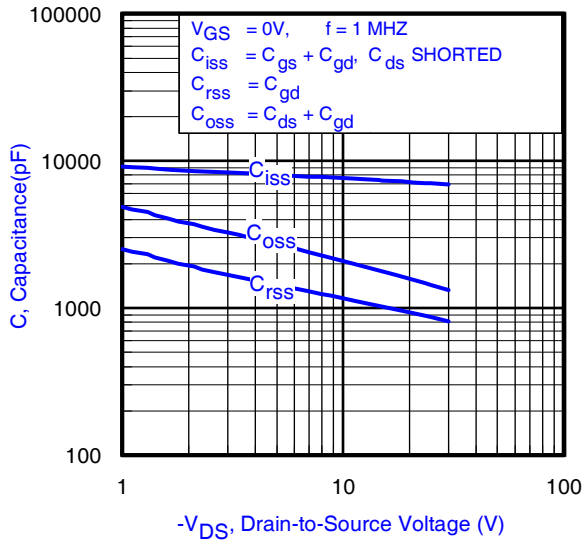



**Fig 8.** Typical Capacitance vs.Drain-to-Source Voltage

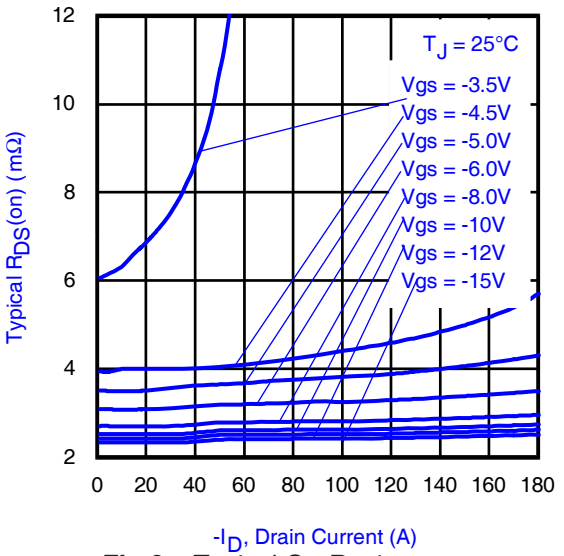



**Fig 9.** Typical On-Resistance vs. Drain Current and Gate Voltage

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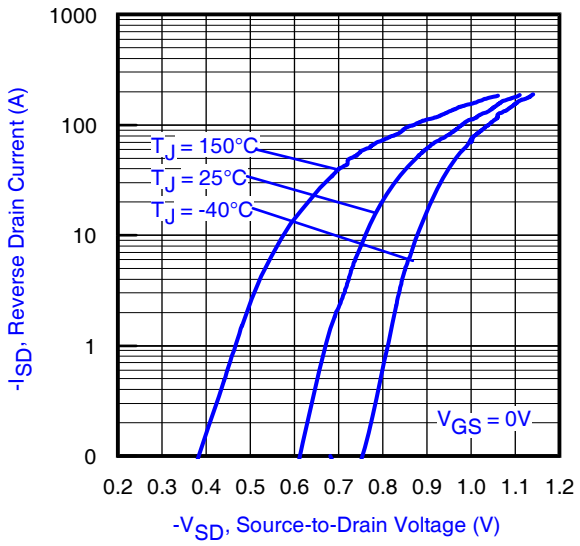


**Fig 10.** Typical Source-Drain Diode Forward Voltage

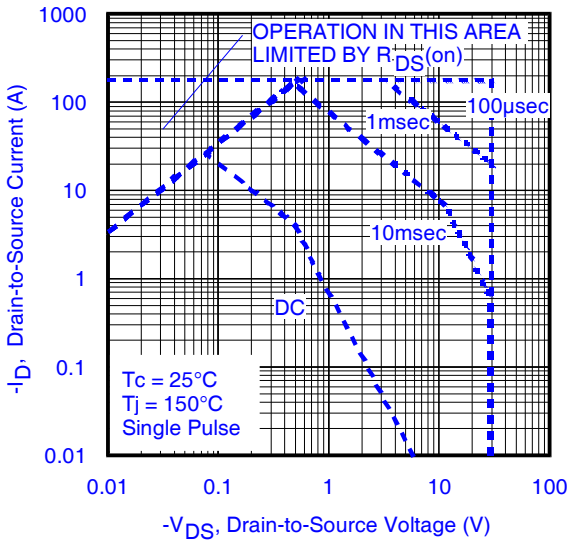


**Fig 11.** Maximum Safe Operating Area

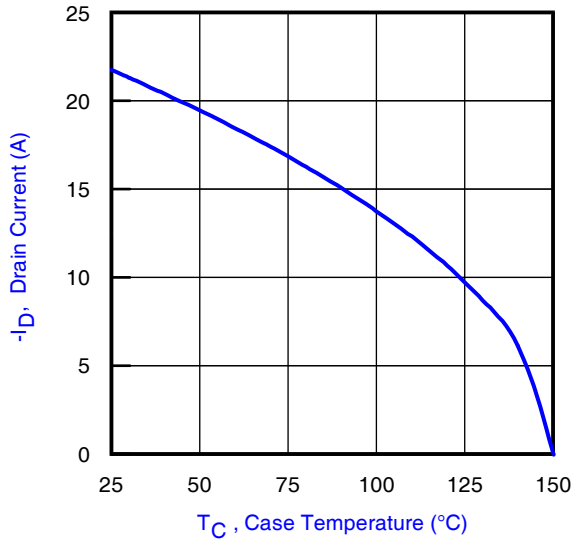


**Fig 12.** Maximum Drain Current vs. Case Temperature

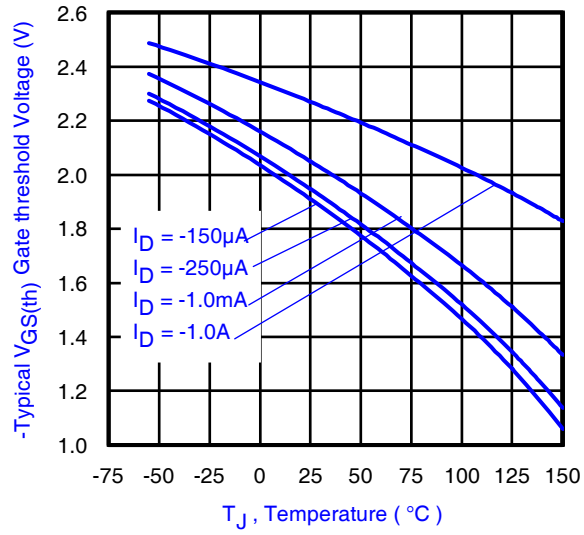


**Fig 13.** Typical Threshold Voltage vs. Junction Temperature

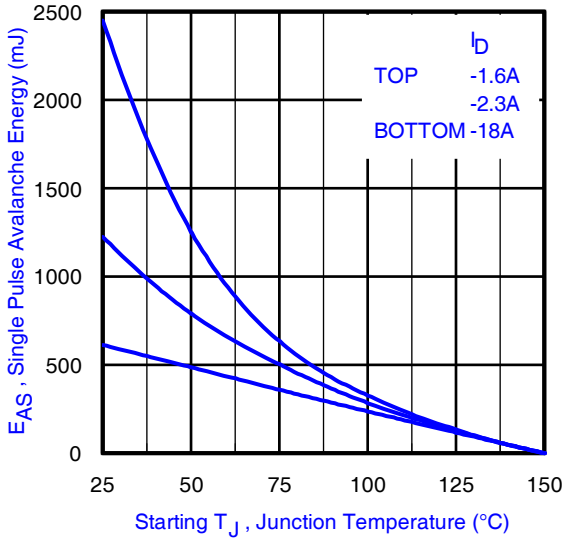


**Fig 14.** Maximum Avalanche Energy vs. Drain Current

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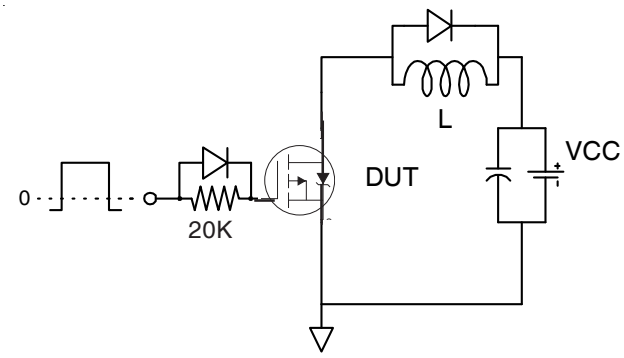


**Fig 17a.** Gate Charge Test Circuit

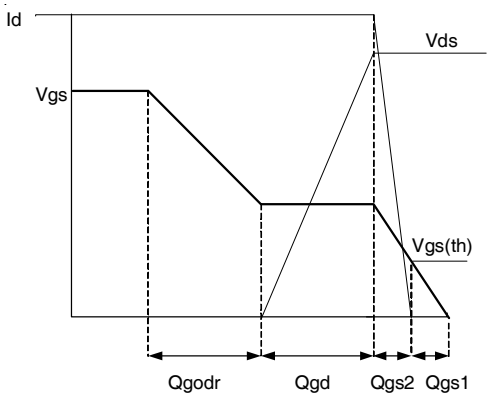


**Fig 17b.** Gate Charge Waveform

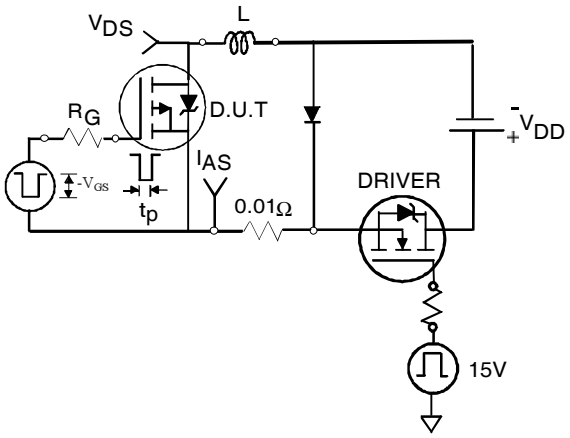


**Fig 18a.** Unclamped Inductive Test Circuit

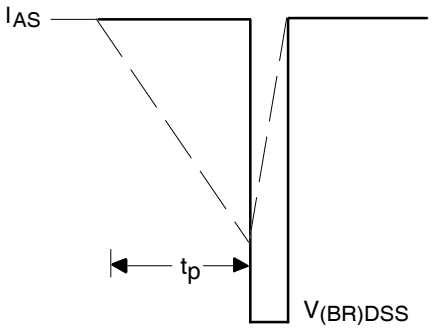


**Fig 18b.** Unclamped Inductive Waveforms

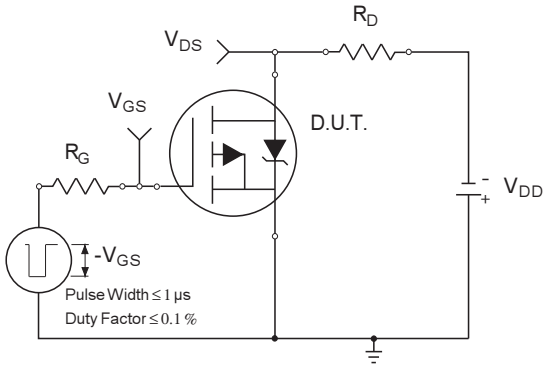


**Fig 19a.** Switching Time Test Circuit

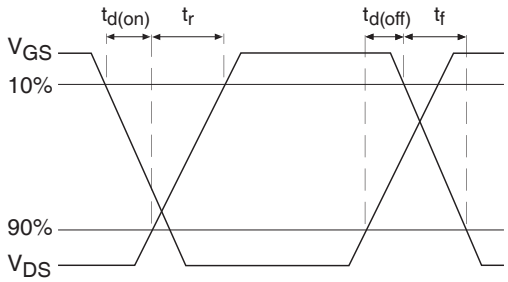


**Fig 19b.** Switching Time Waveforms

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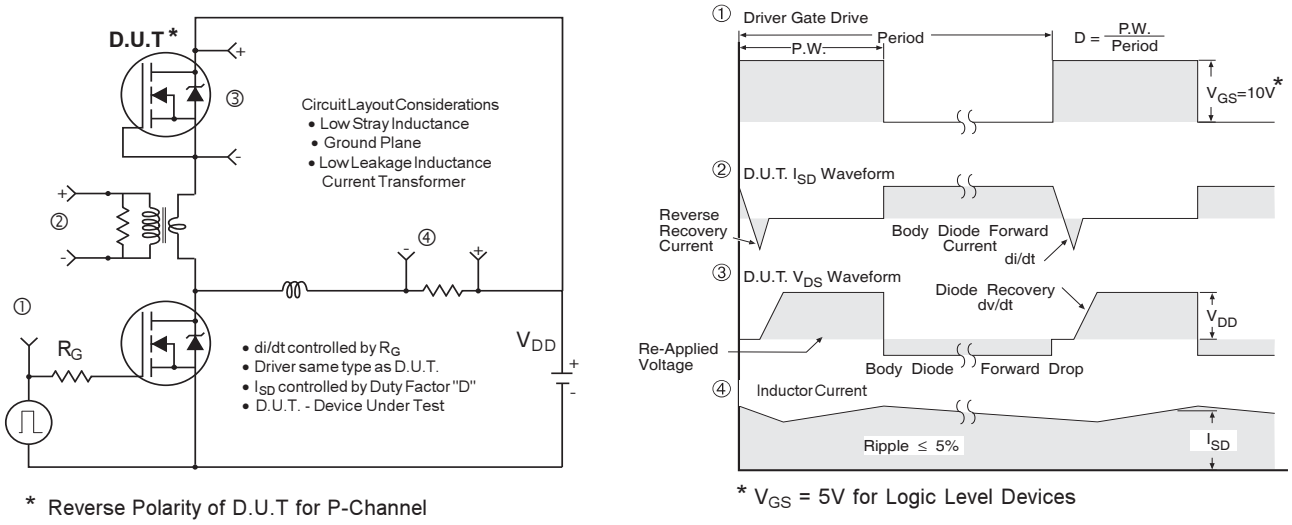
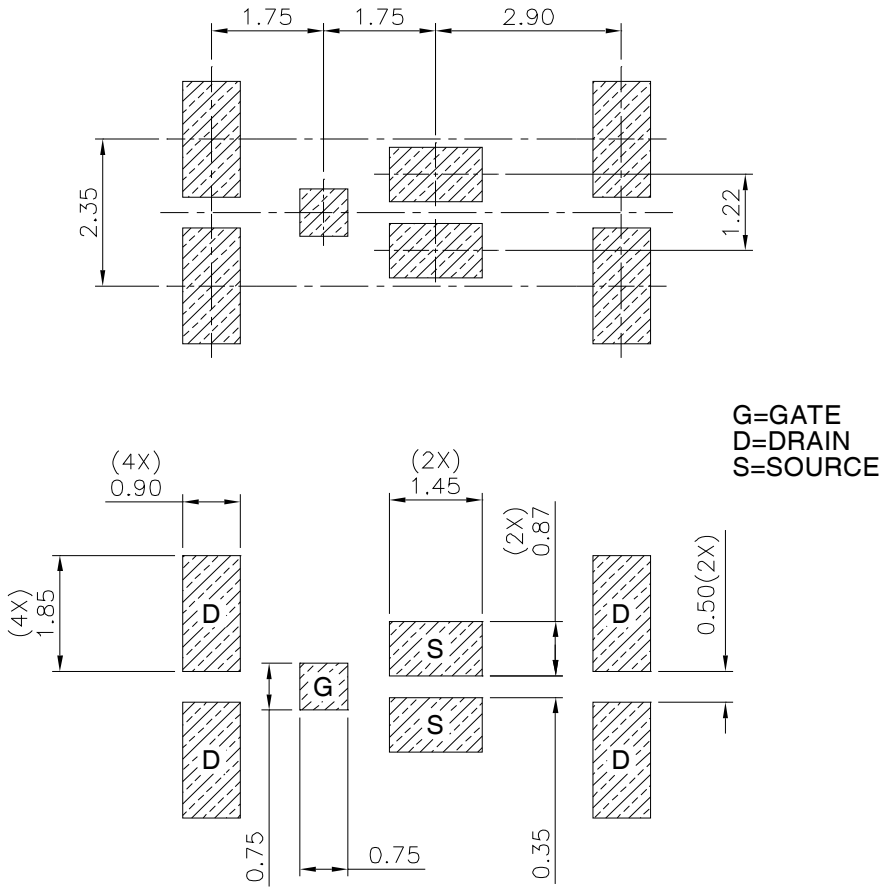



**Fig 20.** Diode Reverse Recovery Test Circuit for P-Channel HEXFET® Power MOSFETs

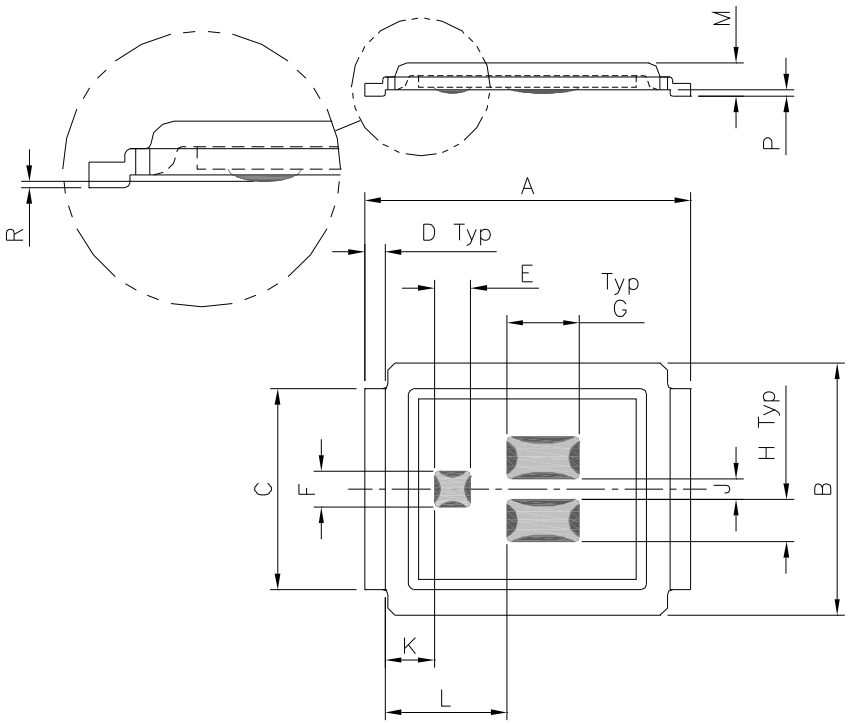
## DirectFET® Board Footprint, MX Outline (Medium Size Can, X-Designation).

Please see DirectFET® application note AN-1035 for all details regarding the assembly of DirectFET®.
This includes all recommendations for stencil and substrate designs.



## DirectFET® Outline Dimension, MX Outline (Medium Size Can, X-Designation).

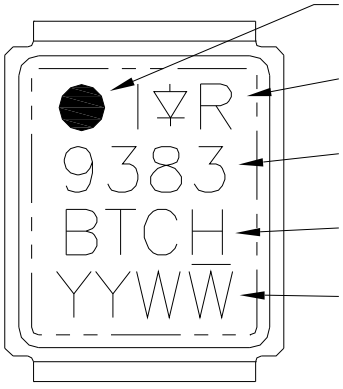
Please see DirectFET® application note AN-1035 for all details regarding the assembly of DirectFET®. This includes all recommendations for stencil and substrate designs.




| DIMENSIONS | | | | |
|---|---|---|---|---|
| | METRIC | | IMPERIAL | |
| CODE | MIN | MAX | MIN | MAX |
| A | 6.25 | 6.35 | 0.246 | 0.250 |
| B | 4.80 | 5.05 | 0.189 | 0.199 |
| C | 3.85 | 3.95 | 0.152 | 0.156 |
| D | 0.35 | 0.45 | 0.014 | 0.018 |
| E | 0.68 | 0.72 | 0.027 | 0.028 |
| F | 0.68 | 0.72 | 0.027 | 0.028 |
| G | 1.38 | 1.42 | 0.054 | 0.056 |
| H | 0.80 | 0.84 | 0.031 | 0.033 |
| J | 0.38 | 0.42 | 0.015 | 0.017 |
| K | 0.88 | 1.02 | 0.035 | 0.040 |
| L | 2.28 | 2.42 | 0.090 | 0.095 |
| M | 0.59 | 0.70 | 0.023 | 0.028 |
| R | 0.03 | 0.08 | 0.001 | 0.003 |
| P | 0.08 | 0.17 | 0.003 | 0.007 |

Dimensions are shown in millimeters (inches)

## DirectFET® Part Marking




GATE MARKING

LOGO

PART NUMBER

BATCH NUMBER

DATE CODE

Line above the last character of the date code indicates "Lead-Free"

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

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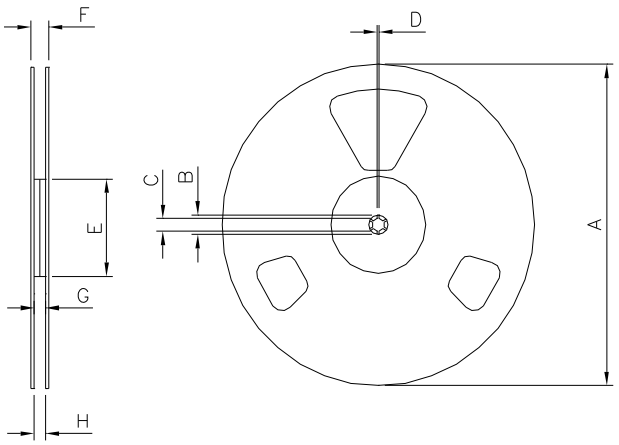
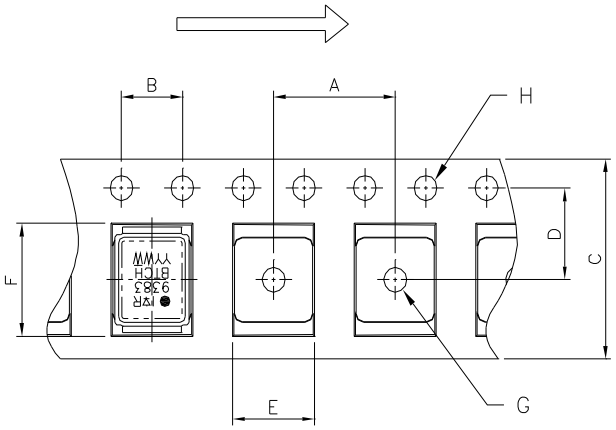
# DirectFET® Tape & Reel Dimension (Showing component orientation).




NOTE: Controlling dimensions in mm
Std reel quantity is 4800 parts. (ordered as IRF9383MTRPBF). For 1000 parts on 7" reel, order IRF9383MTR1PBF

| REEL DIMENSIONS | | | | |
|---|---|---|---|---|
| STANDARD OPTION (QTY 4800) | | | | |
| | METRIC | | IMPERIAL | |
| CODE | MIN | MAX | MIN | MAX |
| A | 330 | N.C | 12.992 | N.C |
| B | 20.2 | N.C | 0.795 | N.C |
| C | 12.8 | 13.2 | 0.504 | 0.520 |
| D | 1.5 | N.C | 0.059 | N.C |
| E | 100.0 | N.C | 3.937 | N.C |
| F | N.C | 18.4 | N.C | 0.724 |
| G | 12.4 | 14.4 | 0.488 | 0.567 |
| H | 11.9 | 15.4 | 0.469 | 0.606 |

LOADED TAPE FEED DIRECTION




NOTE: CONTROLLING DIMENSIONS IN MM

| DIMENSIONS | | | | |
|---|---|---|---|---|
| | METRIC | | IMPERIAL | |
| CODE | MIN | MAX | MIN | MAX |
| A | 7.90 | 8.10 | 0.311 | 0.319 |
| B | 3.90 | 4.10 | 0.154 | 0.161 |
| C | 11.90 | 12.30 | 0.469 | 0.484 |
| D | 5.45 | 5.55 | 0.215 | 0.219 |
| E | 5.10 | 5.30 | 0.201 | 0.209 |
| F | 6.50 | 6.70 | 0.256 | 0.264 |
| G | 1.50 | N.C | 0.059 | N.C |
| H | 1.50 | 1.60 | 0.059 | 0.063 |

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

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**Qualification Information**†

| | | |
|---|---|---|
| Qualification level | Consumer †† (per JEDEC JESD47F††† guidelines) | |
| Moisture Sensitivity Level | DirectFET® | MSL1 (per JEDEC J-STD-020D†††) |
| RoHS Compliant | Yes | |

† Qualification standards can be found at International Rectifier's web site http://www.irf.com/product-info/reliability

†† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information: http://www.irf.com/whoto-call/salesrep/

††† Applicable version of JEDEC standard at the time of product release.

**Revision History**

| Date | Comments |
|---|---|
| 2/17/2014 | • Updated ordering information to reflect the End-Of-life (EOL) of the mini-reel option (EOL notice #264).<br>• Updated data sheet with new IR corporate template. |
| 2/25/2014 | • Change MSL3 to MSL1, on page 9. |
| 6/2/2015 | • Updated schematics from "N-Channel" to "P-Channel" on page 1.<br>• Updated "IFX logo" on page 1 and page 10.. |

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